

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2128	(recrystallizing recrystallization) near8 (semiconductor silicon)	US-PGPU B; USPAT; USOCR	OR	ON	2005/11/02 12:37
L3	564	2 and (remov\$3 near5 oxide)	US-PGPU B; USPAT; USOCR	OR	ON	2005/11/02 12:11
L4	388	3 and (light laser)	US-PGPU B; USPAT; USOCR	OR	ON	2005/11/02 12:37
L5	212	4 and (TFT (thin near5 film near5 transistor))	US-PGPU B; USPAT; USOCR	OR	ON	2005/11/02 12:38
L6	4	((recrystallizing recrystallization) near8 (semiconductor silicon) near8 (remov\$3 near5 oxide))	US-PGPU B; USPAT; USOCR	OR	ON	2005/11/02 12:21
L7	16636	(native natural) near5 oxide	US-PGPU B; USPAT; USOCR	OR	ON	2005/11/02 12:21
L8	914	7 and (TFT (thin near5 film near5 transistor))	US-PGPU B; USPAT; USOCR	OR	ON	2005/11/02 12:22
L9	97	8 and ((recrystallizing recrystallization) near8 (semiconductor silicon))	US-PGPU B; USPAT; USOCR	OR	ON	2005/11/02 12:22
L10	2883	(recrystallizing recrystallization) same (semiconductor silicon)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/02 12:37
L11	580	10 and (light laser)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/02 12:37
L12	85	11 and (TFT (thin near5 film near5 transistor))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/02 12:38